Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Electronic Supplementary Information For

Structural Stability and Electronic Properties of $(SiH)_2O$-formed Siloxene Sheet: A Computational Study

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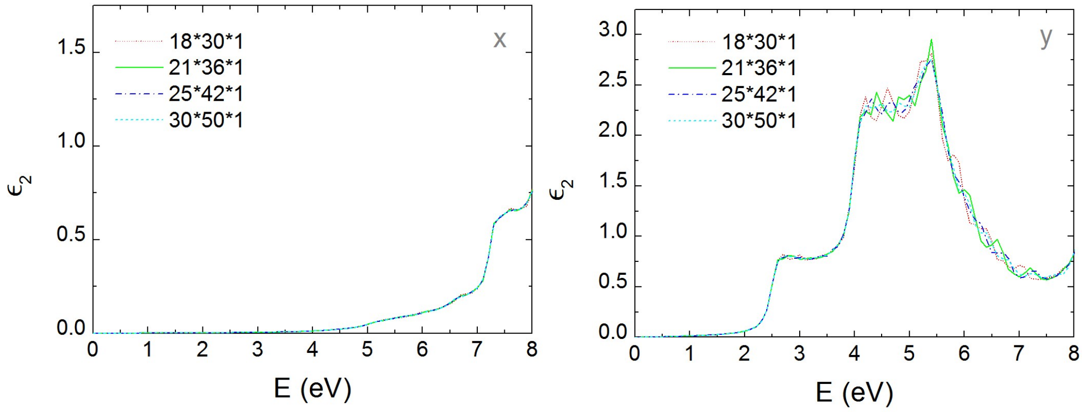

Figure S1: The convergence test for the imaginary part of dielectric function versus the k-point sampling.

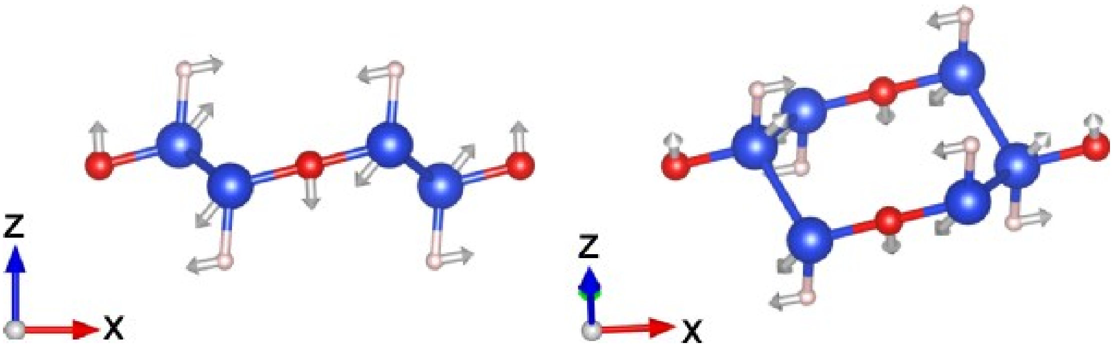

Figure S2: The pictures for the eigenvector of the lowest unstable mode at the □ point in the ideal $(SiH)_2O$ sheet. Arrows stand for the directions of atomic displacements.

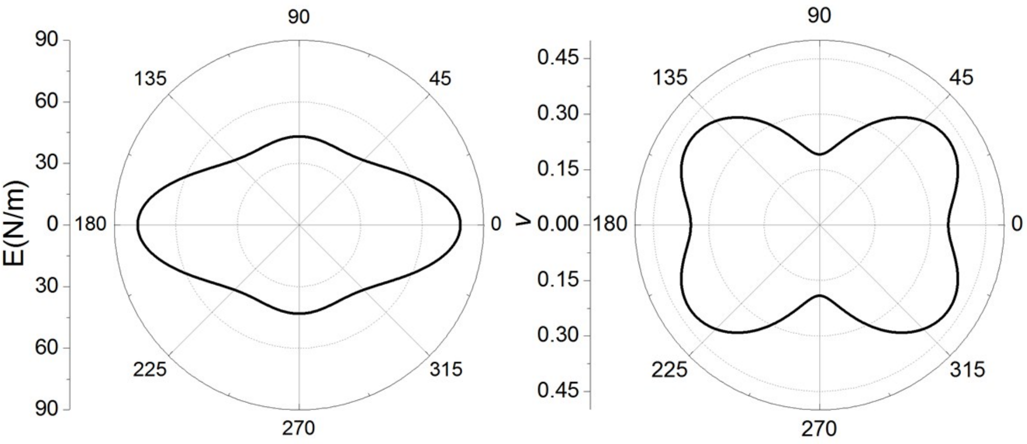

Figure S3: The orientation-dependent Young modulus and Poisson ratio for the ideal $(SiH)_2O$ sheet.